Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (Ultra-High-Speed U-MOSIII)

# **TPC8021-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 3.6 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) =  $13.5 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 19 S$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode:  $V_{th} = 1.1$  to 2.3 V ( $V_{DS} = 10$  V,  $I_{D} = 1$  mA)

### **Absolute Maximum Ratings (Ta = 25°C)**

Characte	eristic	Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V
Gate-source voltage		V <sub>GSS</sub>	±20	< <u>\</u>
Drain current	DC (Note 1)	ID( (	11	A
	Pulsed (Note 1)	₽ N	44	^ \
Drain power dissipation	on (t = 10 s) (Note 2a)	PD	1.9	\\w
Drain power dissipation	on (t = 10 s) (Note 2b)	D	1.0	∑w
Single-pulse avalanch	ne energy (Note 3)	EAS	79	mJ
Avalanche current		IAR	11	Α
Repetitive avalanche energy (Note 2a) (Note 4)		EAR	0.14	mJ
Channel temperature		₹ <sup>T</sup> ch	150	°C
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C
	/ />			

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5.0HO.2

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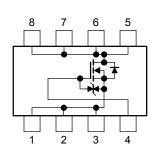
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Weight: 0.085 g (typ.)

### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature,

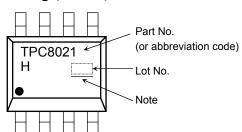
etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient $(t=10 \; s) \eqno(Note \; 2a)$	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

### Marking (Note 5)



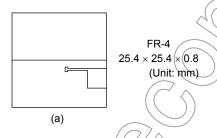
Note: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

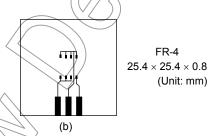
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C,

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = 24 \text{ V}$ ,  $V_{Ch} = 25^{\circ}\text{C}$  (initial), L = 0.5 mH,  $R_{C} = 25^{\circ}\Omega$ ,  $I_{AR} = 11 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: \* Weekly code: (Three digits)

Week of manufacture
(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture
(The last digit of the year)

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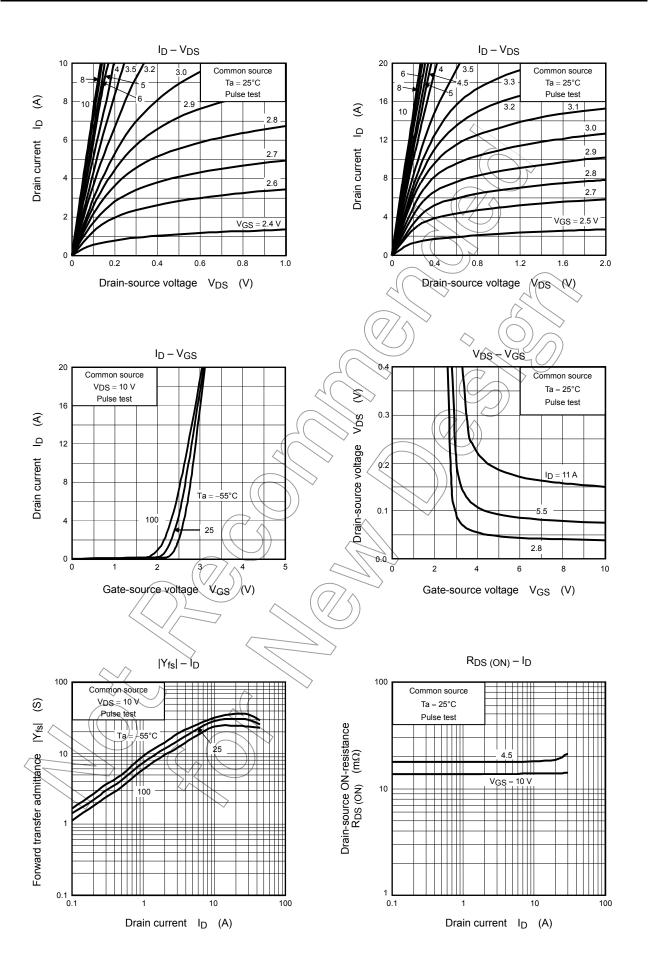
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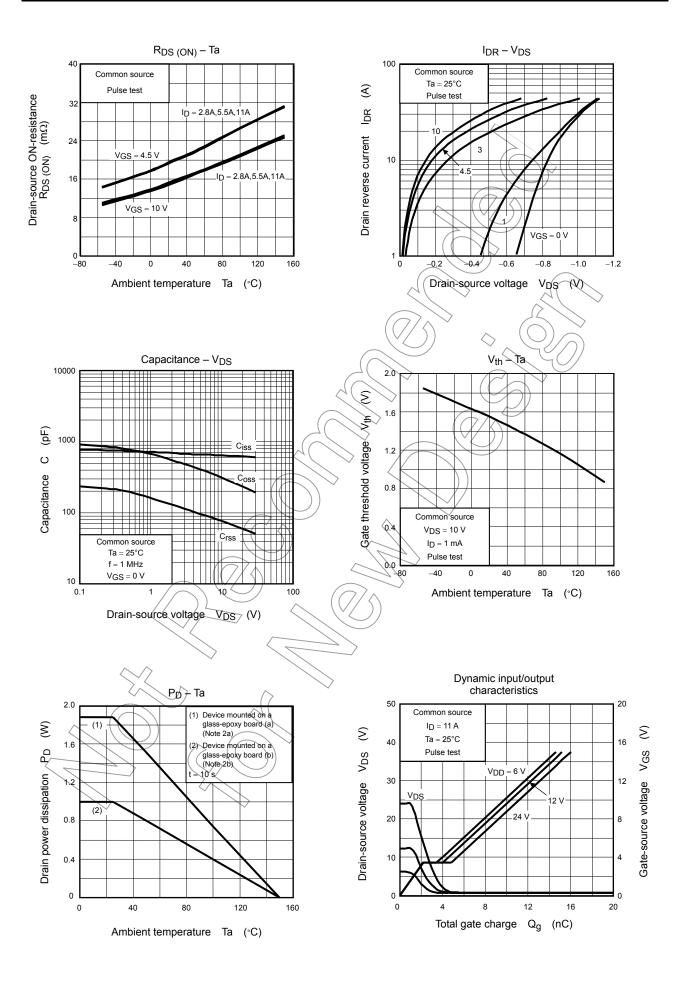
## **Electrical Characteristics (Ta = 25°C)**

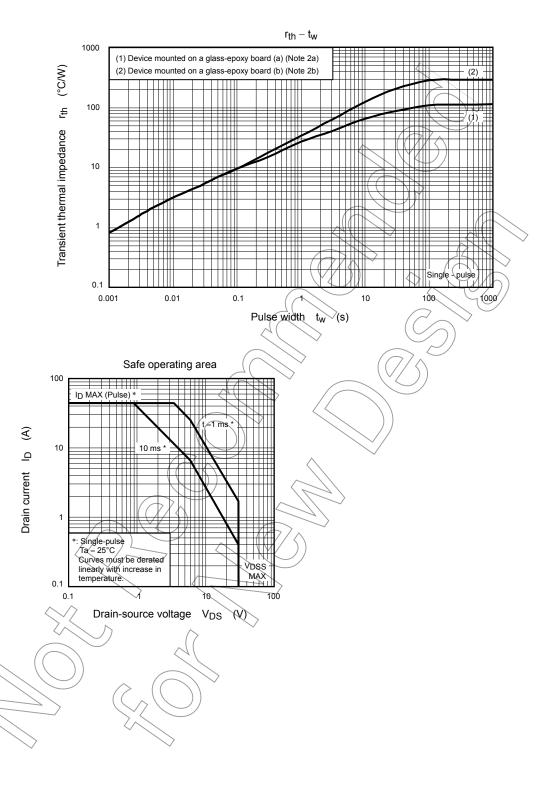
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	μА
Drain-source brea	akdown voltage	V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_		V
Diam-source brea	akdown voltage	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	75	_		V
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	7)	) >	2.3	>
Drain-source ON-resistance		D	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$	) /\	18.5	25	- mΩ
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5.5 A	$\rightarrow$	13.5	17	
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5.5 A	10	19	_	S
Input capacitance	9	C <sub>iss</sub>			640		
Reverse transfer	capacitance	C <sub>rss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	75	/	pF
Output capacitan	ce	Coss			<300	$\rightarrow$	
	Rise time	t <sub>r</sub>	VGS 10 V	-	4	>	
Switching time	Turn-on time	t <sub>on</sub>			8	_	
Switching time	Fall time	t <sub>f</sub>		$(\mathcal{D})$	4	_	ns
	Turn-off time	toff	V <sub>DD</sub> ≈ 15 V Duty ≤ 1%, t <sub>W</sub> = 10 μs	) —	18	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 11 \text{ A}$	_	11	_	
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 11 \text{ A}$	_	6.3	_	
Gate-source char	rge 1	Q <sub>gs1</sub>		_	2.2	_	nC
Gate-drain ("Miller") charge		Qgd	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 11A$	_	2.6	_	
Gate switch charge		Qsw		_	3.6	_	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteri	stic	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	TORP -	_	_	44	Α
Forward voltage (diode)		V <sub>DSF</sub>   I <sub>DR</sub> = 11 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V







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